

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

- 1-6. (Canceled)
7. (Currently Amended) An SOI wafer comprising:  
a support substrate ~~that may be an~~chosen from insulator support  
~~substrates~~substrates and support substrates having insulator layers; and  
at least a silicon active layer formed on the support substrate;  
wherein the silicon active layer of the SOI wafer is formed by bonding to the support substrate, either via an insulator layer or directly to the support substrate for insulator support substrates, a bond wafer that consists of silicon single crystal grown by Czochralski method, that is occupied by a neutral region outside oxidation-induced stacking faults generated in a shape of a ring and that has no defect region detected by Cu deposition method.
8. (Previously Presented) The SOI wafer according to claim 7, wherein a thickness of the silicon active layer is 200 nm or less.
9. (Previously Presented) The SOI wafer according to claim 7, wherein the silicon active layer is formed by being bonded to the support substrate via an oxide film.
10. (Previously Presented) The SOI wafer according to claim 8, wherein the silicon active layer is formed by being bonded to the support substrate via an oxide film.
11. (Previously Presented) The SOI wafer according to claim 9, wherein a thickness of the oxide film is in the range from 2 nm to 3000 nm.
12. (Previously Presented) The SOI wafer according to claim 10, wherein a thickness of the oxide film is in the range from 2 nm to 3000 nm.
13. (Previously Presented) The SOI wafer according to claim 7, wherein the SOI wafer is produced by ion implantation delamination method.

14. (Previously Presented) The SOI wafer according to claim 8, wherein the SOI wafer is produced by ion implantation delamination method.
15. (Previously Presented) The SOI wafer according to claim 9, wherein the SOI wafer is produced by ion implantation delamination method.
16. (Previously Presented) The SOI wafer according to claim 10, wherein the SOI wafer is produced by ion implantation delamination method.
17. (Previously Presented) The SOI wafer according to claim 11, wherein the SOI wafer is produced by ion implantation delamination method.
18. (Previously Presented) The SOI wafer according to claim 12, wherein the SOI wafer is produced by ion implantation delamination method.
19. (Withdrawn) A method for producing an SOI wafer comprising:
  - implanting hydrogen ions, rare gas ions or mixture gas ions of these gases from a surface of a bond wafer to form an ion-implanted layer inside the bond wafer,
  - bonding the surface of the ion-implanted side of the bond wafer and a surface of a base wafer support substrate, said bonding being either via an oxide film or directly, and
  - delaminating a part of the bond wafer at the ion-implanted layer by heat treatment to form an SOI wafer having a silicon active layer, wherein the silicon active layer is formed from the bond wafer that consists of a silicon wafer consisting of silicon single crystal grown by Czochralski method, that is occupied by a neutral region outside oxidation-induced stacking faults generated in a shape of a ring and that has no defect region detected by Cu deposition method.